Proton Displacement Damage

Test Org.*	Device	Function	Technology	Mfr.	Proton Energy (MeV)	Device Xsection (cm^2)	Bits Tested	Bit Xsection (cm^2)	Test Date	LU_{th} (MeV)	LU Xsection (cm^2/bit)	Fac.	Remarks 31-Aug-99
		DRAMs											
	Note: Entries in **RED** indicate data added since the 1997 Compendium.												
ICI	**KM44S16030CT-GL**	**16M x 4 (3.3 V)**	**CMOS**	**SAM**	**30**	**~3.3E-07**			**1998**			**UCD**	**Henson, et al, 99IEEE Wrkshp Rec. Preprint (paper W-7). Static mode. No sat. @ E = 63 MeV. Some stuck bits.**
ICI	**KM44S16030CT-GL**	**16M x 4 (3.3 V)**	**CMOS**	**SAM**	**20**	**~3.1E-07**			**1998**			**UCD**	**Henson, et al, 99IEEE Wrkshp Rec. Preprint (paper W-7). Dynamic mode. Multiple upsets and stuck bits seen . No sat. @ E = 63 MeV.**
ICI	**KM44S32030CT-GL**	**32M x 4 (3.3 V)**	**CMOS**	**SAM**	**~22**	**~3.0E-07**			**1998**			**UCD**	**Henson, et al, 99IEEE Wrkshp Rec. Preprint (paper W-7). Dynamic and static modes. No sat. @ E = 63 MeV.**
Legend:													
	Manufacturers: SAM - Samsung												
	Test Organizations				**Radiation Facilities**								
	ICI - Innovative Concepts Inc., McLean VA				UCD - University of California at Davis, Crocker Nuclear Laboratory, Davis, CA								